



MLL-III-830 /1~2000mW

LOW NOISE INFRARED DIODE LASER AT 830nm

Low noise infrared diode laser at 830nm is made features of high power, long lifetime, low cost and easy operating, which is widely used in measurement, spectrum analysis, etc.



SPECIFICATIONS

Wavelength (nm)	830 ± 10		
Output power (mW)	>1, 10, 50, ..., 2000		
Transverse mode	Near TEM ₀₀		
Operating mode	CW		
Power stability (rms, over 4 hours)	<1%, <3%, <5%		
Noise of amplitude(rms,1~20MHz)	<1%		
Warm-up time (minutes)	<5		
M ² factor	<20		
Warm-up time (minutes)	<10		
Beam divergence, full angle (mrad)	<2.5		
Dimensions of beam at the aperture (mm)	~5×8		
Beam height from base plate (mm)	24.8		
Operating temperature (°C)	10~35		
Power supply (90-264VAC or 5VDC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
Expected lifetime (hours)	10000		
Warranty	1 year		



MxL-III-830	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
<p>139(L)×73(W)×46.2(H) mm³, 0.6kg</p>	<p>153 (L) ×155(W) ×92 (H) mm³, 1.5kg</p>	<p>133 (L) ×130(W) ×65 (H) mm³, 1.2kg</p>	<p>100 (L) ×62(W) ×56 (H) mm³, 0.2kg</p>